

RNA51xx Series

CMOS system-RESET IC

REJ03D0505-0200 Rev.2.00 Sep 13, 2007

General Description

The RNA51xx series provide system reset signal for microprocessor and electrical systems.

Threshold voltage is 1.4 V, 2.6 V, 2.7 V, 2.8 V, 2.9 V, 3.0 V, 3.1 V, 4.4 V, 4.5 V, 4.6 V, 5.0 V and accuracy is ±1.0%.

The reset output delay time can be set by external capacitor connected to CD pin.

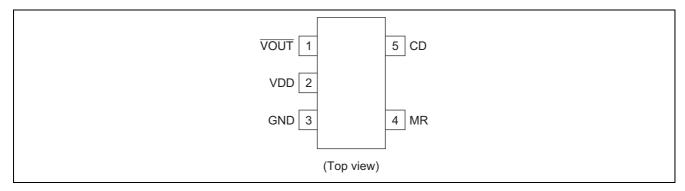
Manual reset input is available and input resistance is 2 M Ω typ.

This series have two output types (active-low CMOS output and active-low open-drain output).

Features

- Threshold voltage: 1.4 V, 2.6 V, 2.7 V, 2.8 V, 2.9 V, 3.0 V, 3.1 V, 4.4 V, 4.5 V, 4.6 V, 5.0 V
- Threshold voltage accuracy: ±1.0%
- Threshold voltage hysteresis: 5% typ.
- Low supply current: 0.7 μA typ.
- Capacitor-adjustable output delay time
- Manual reset
- VOUT CMOS output, or open-drain output
- 5-pin SOT-23 package
- Temperature range: -40°C to 85°C

Pin Arrangement



Applications

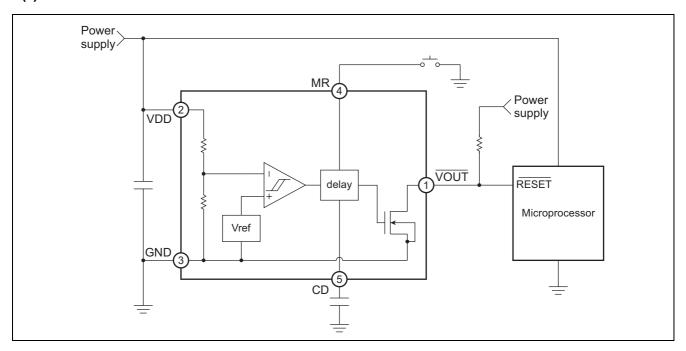
- Power supply voltage monitoring for microprocessors
- Battery-powered portable equipment
- Computers and notebook computers
- Wireless Communication Systems
- Digital still camera, digital video camera, PDA

Product list

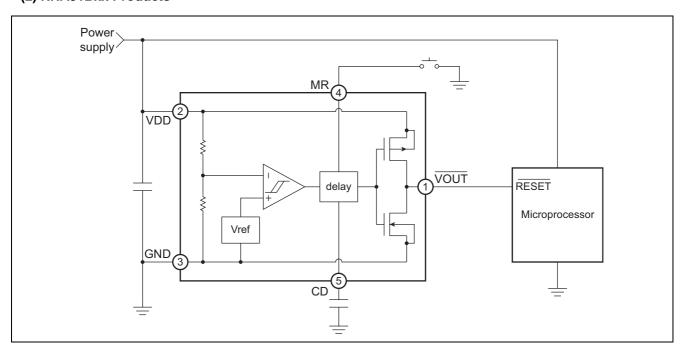
Threshold Voltage –V _{TH}	VOUT				
[V]	Open-Drain output	CMOS output			
1.4	_	RNA51B14FLP			
2.6	RNA51A26FLP	_			
2.7	RNA51A27FLP	RNA51B27FLP			
2.8	RNA51A28FLP	_			
2.9	RNA51A29FLP	_			
3.0	RNA51A30FLP	_			
3.1	RNA51A31FLP	_			
4.4	RNA51A44FLP	_			
4.5	RNA51A45FLP	_			
4.6	RNA51A46FLP	_			
5.0	_	RNA51B50FLP			

Functional block diagram & typical application circuit

(1) RNA51Axx Products



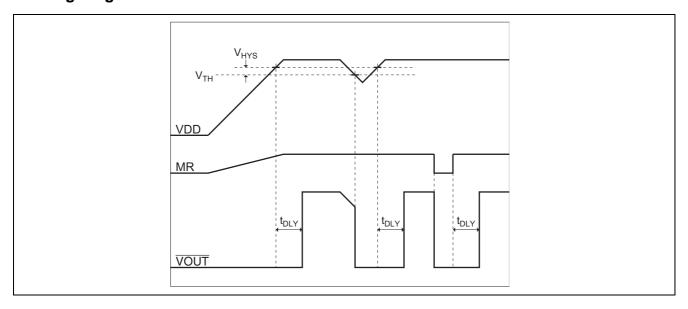
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Notes: 1. It is good for stable operation to use a decoupling capacitor with excellent high frequency characteristics between VDD and GND pin.

2. Capacitor value is determined by system conditions.

Timing Diagram



Absolute Maximum Ratings

(1) RNA51Axx Products

Temperature condition $Ta = 25^{\circ}C$

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Item	Symbol	Pin	Ratings	Unit	
Supply voltage	V_{DD}	V_{DD}	6.0	V	
Output voltage	V _{OUT}	$\overline{V}_{\overline{OUT}}$	-0.3 to 6.0	V	
Input voltage	V_{IN}	MR, MD	-0.3 to V _{DD} +0.3	V	
Output current	I _{OUT}	V _{OUT}	±50	mA	
Continuous power dissipation	P _D	_	120	mW	
Operating temperature range	T_OPR	_	-40 to +85	°C	
Storage temperature range	T _{STG}	_	-55 to +125	°C	

(2) RNA51Bxx Products

Temperature condition $Ta = 25^{\circ}C$

Item	Symbol	Pin	Ratings	Unit	
Supply voltage	V_{DD}	V_{DD}	6.0	V	
Output voltage	V _{OUT}	$\overline{V}_{\overline{OUT}}$	-0.3 to V _{DD} +0.3	V	
Input voltage	V _{IN}	MR, MD	-0.3 to V _{DD} +0.3	V	
Output current	I _{OUT}	V _{OUT}	±50	mA	
Continuous power dissipation	P _D	_	120	mW	
Operating temperature range	T _{OPR}	_	-40 to +85	°C	
Storage temperature range	T _{STG}	_	-55 to +125	°C	

Electrical characteristics

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Temperature condition $Ta = 25^{\circ}C$

Item	Symbol	Min	Тур	Max	Unit	Conditions
Supply voltage	V_{DD}	1.1	_	5.5	V	pull-up resistor = 470 kΩ $V_{OUT} \le 0.1 \times VDD$
Supply current	I _{DD}	_	0.7	4.2	μΑ	V _{DD} = 5.5 V
Threshold voltage	-V _{TH}	-V _{TH} ×0.99	_	-V _{TH} ×1.01	V	
Temperature coefficiency of the thereshold voltage (Reference value)	<u>∆(–V_{тн})</u> –V _{тн} ·∆Та	_	±100	_	ppm/ °C	Ta = -40 to 85°C
Threshold voltage hysteresis	V _{HYS}	-V _{TH} ×3%	-V _{TH} ×5%	-V _{TH} ×8%	V	
VOUT low-level output current	I _{OL}	0.2	1.2	_	mA	$V_{OUT} = 0.5 \text{ V}$ $V_{DD} = 1.3 \text{ V}$
		3.4	7.0	_		$V_{DD} = 2.4 \text{ V} $ $(-V_{TH} \ge 2.7 \text{ V})$
VOUT Output leakage current (open drain output)	I _{LEAK}	_	_	0.1	μА	$V_{DD} = V_{OUT} = 5.5 \text{ V}$
Delay time Note1	t _{DLY}	10	20	35	ms	$V_{DD} = 1.1 \text{ to } 5.5 \text{V}, \ t_{TLH} = 1 \ \mu\text{s}$ $C_D = 4.7 \ \text{nF}$
MR Low-level input voltage Note2	V _{IL}	_	_	V _{DD} ×0.25	V	
MR High-level input voltage	V _{IH}	V _{DD} ×0.75	_	_	V	
MR internal pull-up resistance	R _{MR}	1	2	7	ΜΩ	

(2) RNA51Bxx Products

Temperature condition $Ta = 25^{\circ}C$

Item	Symbol	Min	Тур	Max	Unit	Conditions	
Supply voltage	V_{DD}	1.1	_	5.5	V	pull-up resistor = 470 kΩ $V_{OUT} \le 0.1 \times VDD$	
Supply current	I _{DD}	_	0.7	4.2	μΑ	$V_{DD} = 5.5 \text{ V}$	
Threshold voltage	-V _{TH}	-V _{TH} ×0.99	_	-V _{TH} ×1.01	V		
Threshold voltage temperature dependency (Reference value for design)	<u>∆(−V_{тн})</u> −V _{тн} ·∆Та	_	±100	_	ppm/ °C	Ta = -40 to 85°C	
Threshold voltage hysteresis	V _{HYS}	-V _{TH} ×3%	–V _{TH} ×5%	-V _{TH} ×8%	V		
VOUT low-level output current	I _{OL}	0.2	1.2	_	mA	$V_{OUT} = 0.5 \text{ V}$ $V_{DD} = 1.3 \text{ V}$	
		3.4	7.0	_		$V_{DD} = 2.4 \text{ V} $ $(-V_{TH} \ge 2.7 \text{ V})$	
VOUT High-level output current (CMOS output)	I _{OH}	-1.4	-2.7	_	mA	$V_{OUT} = V_{DD} = 4.5 \text{ V} $ $V_{DD} = 0.5 \text{ V} $ $(-V_{TH} \le 4.0 \text{ V})$	
		-1.5	-3.0	_		$V_{DD} = 5.5 \text{ V}$	
Delay time Note1	t _{DLY}	10	20	35	ms	$V_{DD} = 1.1 \text{ to } 5.5 \text{ V}, t_{TLH} = 1 \mu\text{s}$ $C_D = 4.7 \text{ nF}$	
MR Low-level input voltage Note2	V _{IL}	_	_	V _{DD} ×0.25	V		
MR High-level input voltage	V _{IH}	V _{DD} ×0.75	_	_	V		
MR internal pull-up resistance	R _{MR}	1	2	7	МΩ		

Note:

- 1. Delay time is specified when charging starts in the condition that CD pin is completely discharged. When discharging of CD pin is not complete because of immediate stop and other reasons, the delay time is not guaranteed. Therefore, when passing of VDD pin input voltage immediately stops (the period of condition that VDD pin input voltage is lower than the detected voltage is short), discharging of external capacitor CD is inadequate, and the delay time becomes much shorter than the minimum guaranteed value. Be sure to fully check that there are no problems as the system.
- 2. Minimum value of low-pulse width to be input to MR pin depends on the value of external capacitor CD. Therefore, set the low-pulse width to be input to MR pin to the minimum input low-pulse width shown in figure 1 or more.

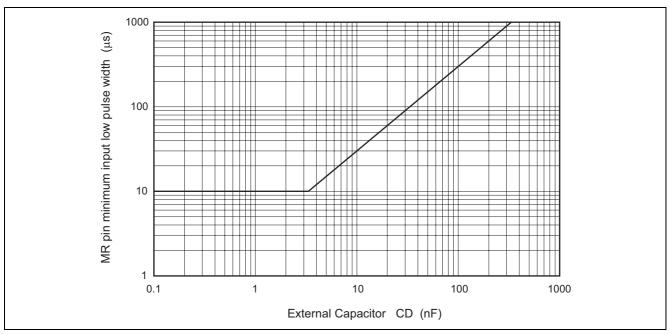


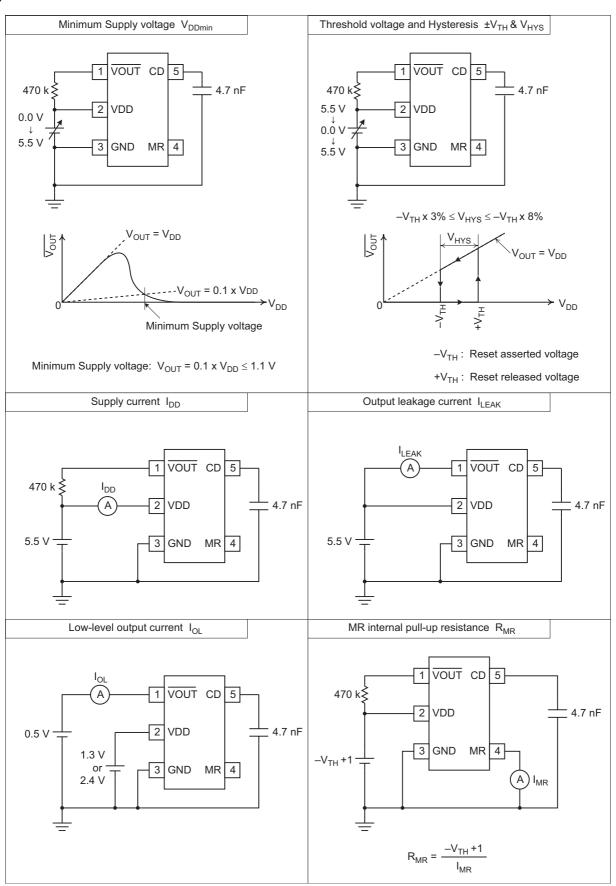
Figure 1 Dependence of MR pin minimum input low pulse width and external capacitor CD

Pin Description

PIN	NAME	FUNCTION
1	VOUT	VOUT changes from high to low whenever VDD drops below –V _{TH} .
		A pull-up resistor from 470 k Ω to 1 M Ω should be used on this pin for open-drain output.
2	VDD	Supply voltage and input for voltage detector.
		A decoupling capacitor with excellent high frequency characteristics should be placed near VDD
		pin and connected between VDD and GND pin.
3	GND	Ground
4	MR	Active-low Manual Reset Input. VOUT is low-level while MR is low.
		Once MR is disabling, VOUT turn to high-level after delay time.
		MR pin is internally pulled up to VDD through 2 M Ω .
5	CD	Connect capacitor between CD and GND pin to set programmable delay time.
		Ceramic capacitor from 100 pF to 0.1 µF is recommended.

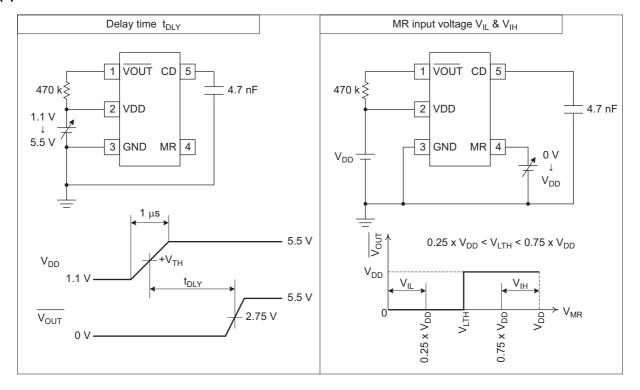
Test Circuit

(1) RNA51Axx Products



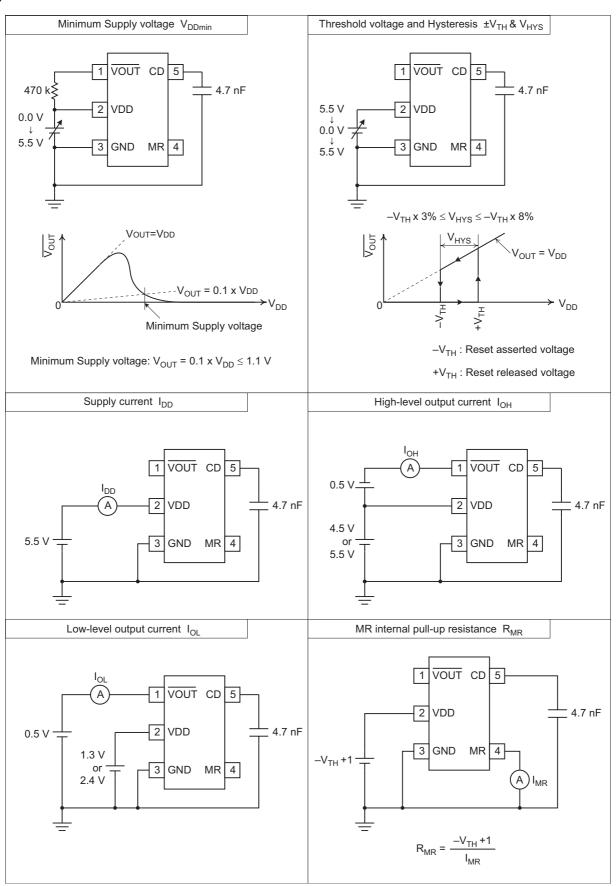
Test Circuit (Cont.)

(1) RNA51Axx Products



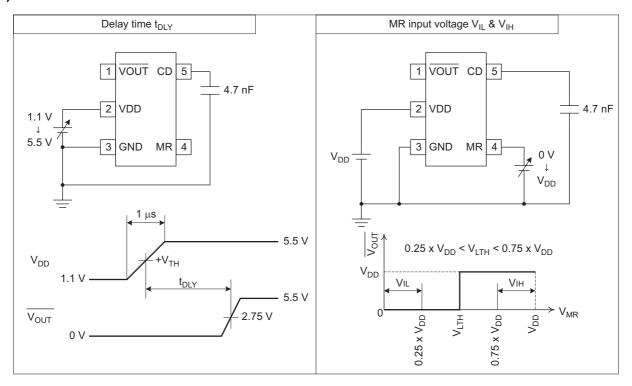
Test Circuit (Cont.)

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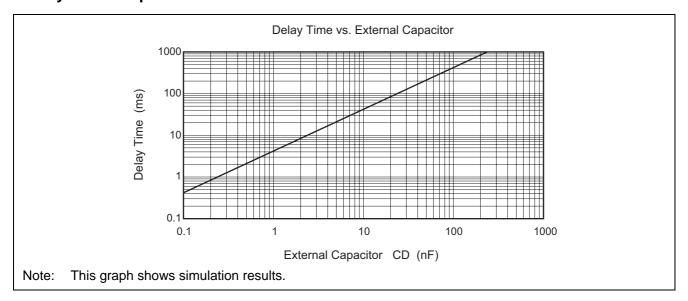


Test Circuit (Cont.)

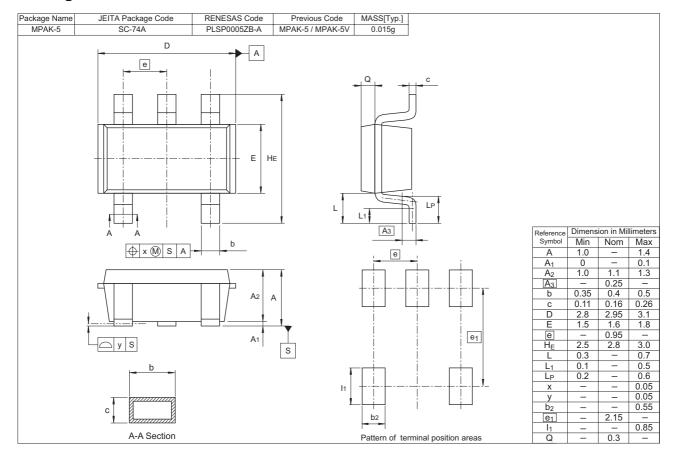
(2) RNA51Bxx Products



Delay Time Graph



Package Dimensions



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